

Data sheet acquired from Harris Semiconductor SCHS199

February 1998

建多邦, 专业PCB打样工厂, 24小时加急出货 CD74HC4016

High-Speed CMOS Logic Quad Bilateral Switch

Features

•	Wide Analog-Input-Voltage Range 0V to 10
•	Low "ON" Resistance
	- 45Ω (Typ)V _{CC} = 4.5
	- 35Ω (Typ)V _{CC} = 6 ¹
	- 30Ω (Typ)1fcV _{CC} = 9'

- Fast Switching and Propagation Delay Times
- Low "OFF" Leakage Current
- Built-In "Break-Before-Make" Switching
- Suitable for Sample and Hold Applications
- Wide Operating Temperature Range . . . -55°C to 125°C
- HC Types
 - 2V to 10V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} at V_{CC} = 5V

Description

The Harris CD74HC4016 contains four independent digitally controlled analog switches that use silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

Each switch has two input/output terminals (nY, nZ) and an active high enable input (nE). Current through the switch will not cause additional V_{CC} current provided the analog voltage is maintained between V_{CC} and GND.

Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CD74HC4016E	-55 to 125	14 Ld PDIP	E14.3
CD74HC4016E	-55 to 125	14 Ld SOIC	M14.15

NOTES:

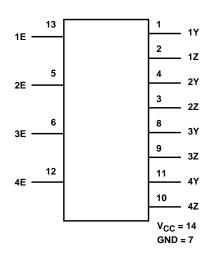
- When ordering, use the entire part number. Add the suffix 96 to obtain the variant in the tape and reel.
- Wafer and die for this part number is available which meets all electrical specifications. Please contact your local sales office or Harris customer service for ordering information.

Pinout

CD74HC4016 (PDIP) TOP VIEW 1Y 1 14 V_{CC} 1Z 2 13 1E 2Z 3 12 4E 2Y 4 11 4Y 2E 5 10 4Z 3E 6 9 3Z GND 7 8 3Y



Functional Diagram



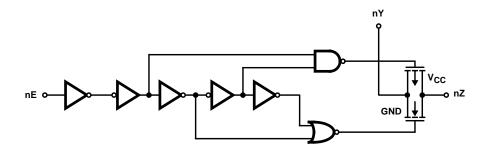
TRUTH TABLE

INPUT nE	SWITCH
L	OFF
Н	ON

NOTE:

H = High Level Voltage L = Low Level Voltage

Logic Diagram



Absolute Maximum Ratings

DC Supply Voltage, V $_{CC}$... -0.5V to 7V DC Input Diode Current, I $_{IK}$ For V $_{I}$ < -0.5V or V $_{I}$ > V $_{CC}$ + 0.5V ... ± 20 mA DC Drain Current, per Output, I $_{O}$ For -0.5V < V $_{O}$ < V $_{CC}$ + 0.5V ... ± 25 mA DC Output Diode Current, I $_{OK}$ For V $_{O}$ < -0.5V or V $_{O}$ > V $_{CC}$ + 0.5V ... ± 20 mA DC Output Source or Sink Current per Output Pin, I $_{O}$ For V $_{O}$ > -0.5V or V $_{O}$ < V $_{CC}$ + 0.5V ... ± 25 mA DC V $_{CC}$ or Ground Current, I $_{CC}$... ± 25 mA

Thermal Information

Thermal Resistance (Typical, Note 3)	θ _{JA} (^o C/W)
PDIP Package	. 90
Maximum Junction Temperature (Plastic Package)	150 ⁰ C
Maximum Storage Temperature Range	65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300 ^o C

Operating Conditions

Temperature Range, T _A 55°C to 125°C
Supply Voltage Range, V _{CC}
HC Types2V to 10\
DC Input or Output Voltage, V _I , V _O
Input Rise and Fall Time
2V
4.5V 500ns (Max
6V
9V

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

3. θ_{JA} is measured with the component mounted on an evaluation PC board in free air.

DC Electrical Specifications

		TES	CONDIT	IONS		25°C		-40°C T	O 85°C	-55°C T	O 125°C	
PARAMETER	SYMBOL	V _I (V)	V _{IS} (V)	V _{CC} (V)	MIN	TYP	МАХ	MIN	MAX	MIN	MAX	UNITS
HC TYPES												
High Level Input	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
Voltage				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
"ON" Resistance	ON	V _{IH} or V _{IL}	V _{IH} or V _{CC} or GND	4.5	-	45	180	-	225	-	270	Ω
I _O = 1mA				6	-	35	160	-	200	-	240	Ω
				9	-	30	135	-	170	-	205	Ω
				4.5	-	85	320	-	400	-	480	Ω
				6	-	55	240	-	300	-	360	Ω
				9	-	35	170	-	215	-	255	Ω
Maximum "ON"	ΔR_{ON}	V _{IL} or	V _{CC} or	4.5	-	10	-	-	-	-	-	Ω
Resistance Between Any Two Switches		V _{IH}	GND	6	-	8.5	-	-	-	-	-	Ω
Switch Off Leakage	I _{IZ}	En =	V _{CC} or	6	-	-	±0.1	-	±1	-	±1	μА
Current		GND	GND	10	-	-	±0.1	-	±1	-	±1	μА
Logic Input Leakage Current	lı	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μА

DC Electrical Specifications (Continued)

		TEST CONDITIONS			25°C		-40°C TO 85°C		-55°C TO 125°C			
PARAMETER	SYMBOL	V _I (V)	V _{IS} (V)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Quiescent Device	Icc	V _{CC} or	V _{CC} or	6	-	-	2	-	20	-	40	μΑ
Current I _O = 0mA		GND	GND	10	-	-	16	-	160	-	320	μА

NOTE: For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

Switching Specifications Input t_r, t_f = 6ns

		TEST	TEST V _{CC}		25°C		-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	TYP	МАХ	MIN	MAX	MIN	MAX	UNITS
HC TYPES											
Propagation Delay, Switch In to Switch Out	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	-	60	-	75	-	90	ns
Switch in to Switch Out			4.5	-	-	12	-	15	-	18	ns
		C _L = 15pF	5	-	4	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	10	-	13	-	15	ns
			9	-	-	8	-	10	-	12	ns
Propagation Delay,	t _{PZH} , t _{PZL}	C _L = 50pF	2	-	-	190	-	240	-	285	ns
Switch Turn-On En to Out			4.5	-	-	38	-	48	-	57	ns
		C _L = 15pF	5	-	16	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	32	-	41	-	48	ns
			9	-	-	28	-	35	-	42	ns
Propagation Delay,	t _{PHZ} , t _{PLZ}	C _L = 50pF	2	-	-	145	-	180	-	220	ns
Switch Turn-Off En to Out			4.5	-	-	29	-	36	-	44	ns
		C _L = 15pF	5	-	12	-	-	-	-	-	ns
		C _L = 50pF	6	-	-	25	-	31	-	38	ns
			9	-	-	22	-	28	-	33	ns
Input Capacitance	Cl	-	-	-	-	10	-	10	-	10	pF
Power Dissipation Capacitance (Notes 4, 5)	C _{PD}	-	5	-	12	-	-	-	-	-	pF

NOTES:

- 4. $C_{\mbox{PD}}$ is used to determine the dynamic power consumption, per package.
- 5. $P_D = C_{PD} \ V_{CC}^2 \ f_i + \Sigma \ (C_L + C_S) \ V_{CC}^2 \ f_o$ where f_i = input frequency, f_o = output frequency, C_L = output load capacitance, C_S = switch capacitance, V_{CC} = supply voltage.

Analog Channel Specifications $T_A = 25^{\circ}C$

PARAMETER	TEST CONDITIONS	V _{CC} (V)	CD74HC4016	UNITS
Switch Frequency Response Bandwidth at -3dB Figure 3	Figure 6, Notes 6, 7	4.5	>200	MHz
Crosstalk Between Any Two Switches, Figure 4	Figure 5, Notes 7, 8	4.5	TBE	dB
Total Harmonic Distortion	1kHz, V _{IS} = 4V _{P-P} Figure 7	4, 5	0.078	%
	1kHz, V _{IS} = 8V _{P-P} Figure 7	9	0.018	%

Analog Channel Specifications $T_A = 25^{\circ}C$ (Continued)

PARAMETER	TEST CONDITIONS	V _{CC} (V)	CD74HC4016	UNITS
Control to Switch Feedthrough Noise	Figure 8	4.5	TBE	mV
		9	TBE	mV
Switch "OFF" Signal Feedthrough, Figure 4	Figure 9, Notes 7, 8	4.5	-62	dB
Switch Input Capacitance, C _S		-	5	pF

NOTES:

- 6. Adjust input level for 0dBm at output, f = 1MHz.
- 7. V_{IS} is centered at $V_{CC}/2$.
- 8. Adjust input for 0dBm at V_{IS}.

Typical Performance Curves

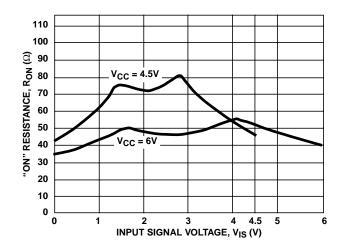


FIGURE 1. TYPICAL "ON" RESISTANCE vs INPUT SIGNAL VOLTAGE

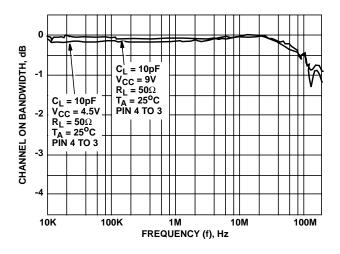


FIGURE 3. SWITCH FREQUENCY RESPONSE

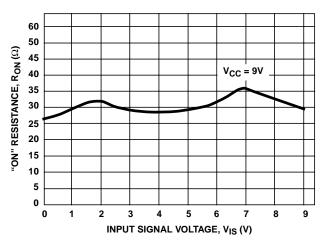


FIGURE 2. TYPICAL "ON" RESISTANCE vs INPUT SIGNAL VOLTAGE

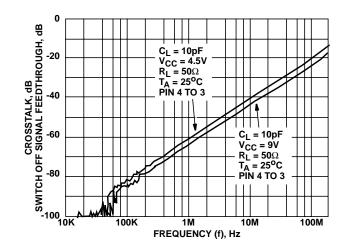
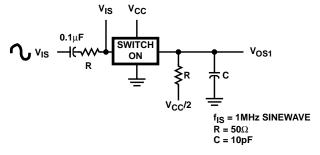


FIGURE 4. SWITCH-OFF SIGNAL FEEDTHROUGH AND CROSSTALK vs FREQUENCY

Analog Test Circuits



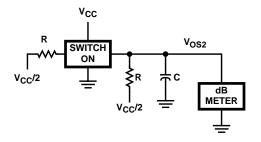
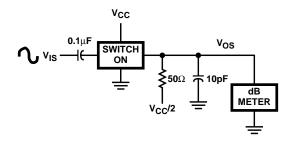


FIGURE 5. CROSSTALK BETWEEN TWO SWITCHES TEST CIRCUIT



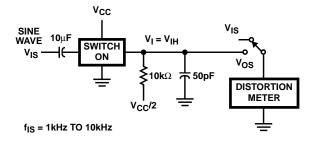
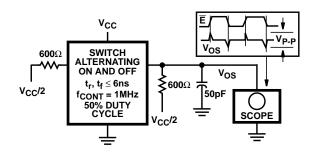


FIGURE 6. FREQUENCY RESPONSE TEST CIRCUIT

FIGURE 7. TOTAL HARMONIC DISTORTION TEST CIRCUIT



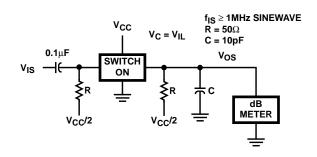
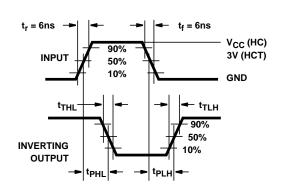


FIGURE 8. CONTROL-TO-SWITCH FEEDTHROUGH NOISE TEST CIRCUIT

FIGURE 9. SWITCH OFF SIGNAL FEEDTHROUGH

Test Circuits and Waveforms



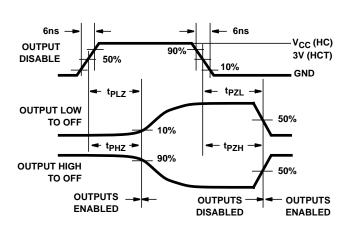


FIGURE 10. HC/HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

FIGURE 11. SWITCH TURN-ON AND TURN OFF PROPAGATION DELAY TIMES

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